

☐ An additional claim fee is required, and is calculated as shown below:

AMENDED CLAIMS					
	NO. OF CLAIMS	HIGHEST NO. OF CLAIMS PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	ADDT'L FEE
Total Claims	20	MINUS 20 =	0	× \$18.00 (103) =	0.00
Independent Claims	3	MINUS 3 =	0	× \$80.00 (102) =	0.00
If Amendment adds multiple dependent claims, add \$270.00 (104)					
Total Amendment Fee					0.00
If small entity status is claimed, subtract 50% of Total Amendment Fee					
TOTAL ADDITIONAL FEE DUE FOR THIS AMENDMENT					0.00

☐ A claim fee in the amount of \$_____ is enclosed.

☐ Charge \$_____ to Deposit Account No. 02-4800.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17, 1.20(d) and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

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By: _____

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Date: October 13, 2000



#19

Patent
Attorney's Docket No. 015290-238

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Jeffrey HUNG et al.) Group Art Unit: 1765
Application No.: 09/002,007) Examiner: L. Vinh
Filed: December 31, 1997)
For: ETCHING PROCESS FOR ORGANIC)
ANTI-REFLECTIVE COATING)

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Official Action dated July 13, 2000, please amend the above-identified application as follows.

REMARKS

Favorable reconsideration of this application in light of the following remarks is respectfully requested.

The present invention broadly relates to etching an organic anti-reflective coating (ARC). In particular, the present invention sets forth a process for removing exposed areas of an organic ARC on a metallic layer, the exposed areas of the ARC having been exposed by previously etching a photoresist covering the ARC. The process comprises exposing the exposed areas of the ARC to an oxygen-free system of etching agents in an ionized state in

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